

Low power JFET dual operational amplifiers

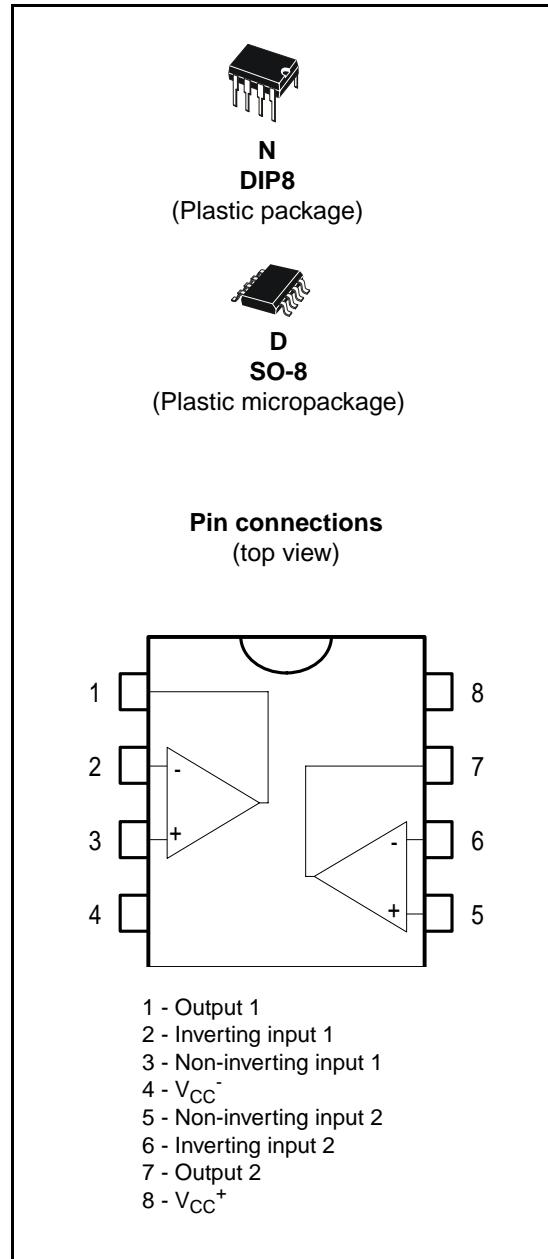
Features

- Very low power consumption : 200 μ A
- Wide common-mode (up to V_{CC}^+) and differential voltage ranges
- Low input bias and offset currents
- Output short-circuit protection
- High input impedance JFET input stage
- Internal frequency compensation
- Latch up free operation
- High slew rate : 3.5V/ μ s

Description

The TL062, TL062A and TL062B are high-speed JFET input single operational amplifiers. Each of these JFET input operational amplifiers incorporates well matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.



2 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TL062M, AM, BM	TL062I, AI, BI	TL062C, AC, BC	
V_{CC}	Supply voltage ⁽¹⁾	± 18			V
V_i	Input voltage ⁽²⁾	± 15			V
V_{id}	Differential input voltage ⁽³⁾	± 30			V
P_{tot}	Power dissipation	680			mW
	Output short-circuit duration ⁽⁴⁾	Infinite			
T_{stg}	Storage temperature range	-65 to +150	-65 to +150	-65 to +150	°C
R_{thja}	Thermal resistance junction to ambient ^{(5) (6)} SO-8 DIP8	125 85			°C/W
R_{thjc}	Thermal resistance junction to case ^{(5) (6)} SO-8 DIP8	40 41			°C/W
ESD	HBM: human body model ⁽⁷⁾	900			V
	MM: machine model ⁽⁸⁾	150			V
	CDM: charged device model ⁽⁹⁾	1.5			kV

1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}^+ and V_{CC}^- .
2. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
3. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.
5. Short-circuits can cause excessive heating and destructive dissipation.
6. R_{th} are typical values.
7. Human body model: 100pF discharged through a 1.5kΩ resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
8. Machine model: a 200pF cap is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5Ω), done for all couples of pin combinations with other pins floating.
9. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Table 2. Operating conditions

Symbol	Parameter	TL062M, AM, BM	TL062I, AI, BI	TL062C, AC, BC	Unit
V_{CC}	Supply voltage range	6 to 36			V
T_{oper}	Operating free-air temperature range	-55 to +125	-40 to +105	0 to +70	°C

3 Electrical characteristics

Table 3. $V_{CC} = \pm 15V$, $T_{amb} = +25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TL062M			TL062I			TL062C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{io}	Input offset voltage ($R_S = 50\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		3	6 15		3	6 9		3	15 20	mV
DV_{io}	Temperature coefficient of input offset voltage ($R_S = 50\Omega$)		10			10			10		$\mu V/^{\circ}C$
I_{io}	Input offset current ⁽¹⁾ $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 20		5	100 10		5	200 5	pA nA
I_{ib}	Input bias current ⁽¹⁾ $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		30	200 50		30	200 20		30	400 10	pA nA
V_{icm}	Input common mode voltage range	± 11.5	$+15$ -12		± 11.5	$+15$ -12		± 11	$+15$ -12		V
V_{opp}	Output voltage swing ($R_L = 10k\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	20 20	27		20 20	27		20 20	27		V
A_{vd}	Large signal voltage gain $R_L = 10k\Omega$, $V_o = \pm 10V$, $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	4 4	6		4 4	6		3 3	6		V/mV
GBP	Gain bandwidth product $T_{amb} = +25^{\circ}C$, $R_L = 10k\Omega$, $C_L = 100pF$		1			1			1		MHz
R_i	Input resistance		10^{12}			10^{12}			10^{12}		Ω
CMR	Common mode rejection ratio $R_S = 50\Omega$	80	86		80	86		70	76		dB
SVR	Supply voltage rejection ratio $R_S = 50\Omega$	80	95		80	95		70	95		dB
I_{cc}	Supply current, no load $T_{amb} = +25^{\circ}C$, no load, no signal		200	250		200	250		200	250	μA
V_{o1}/V_{o2}	Channel separation $A_v = 100$, $T_{amb} = 25^{\circ}C$		120			120			120		dB
P_D	Total power consumption $T_{amb} = +25^{\circ}C$, no load, no signal		6	7.5		6	7.5		6	7.5	mW
SR	Slew rate $V_i=10V$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_v=1$	1.5	3.5		1.5	3.5		1.5	3.5		$V/\mu s$

Table 3. $V_{CC} = \pm 15V$, $T_{amb} = +25^{\circ}C$ (unless otherwise specified) (continued)

Symbol	Parameter	TL062M			TL062I			TL062C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_r	Rise time $V_i = 20mV$, $R_L = 10k\Omega$ $C_L = 100pF$, $A_v = 1$		0.2			0.2			0.2		μs
K_{ov}	Overshoot factor (see <i>Figure 15</i>) $V_i = 20mV$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_v = 1$		10			10			10		%
e_n	Equivalent input noise voltage $R_S = 100\Omega$, $f = 1kHz$		42			42			42		$\frac{nV}{\sqrt{Hz}}$

1. The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

Table 4. $V_{CC} = \pm 15V$, $T_{amb} = +25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TL062AC, AI, AM			TL062BC, BI, BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input offset voltage ($R_S = 50\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		3	6 7.5		2	3 5	mV
DV_{io}	Temperature coefficient of input offset voltage ($R_S = 50\Omega$)		10			10		$\mu V/^{\circ}C$
I_{io}	Input offset current ⁽¹⁾ $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 3		5	100 3	pA nA
I_{ib}	Input bias current ⁽¹⁾ $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$		30	200 7		30	200 7	nA
V_{icm}	Input common mode voltage range	± 11.5	+15 -12		± 11.5	+15 -12		
V_{opp}	Output voltage swing ($R_L = 10k\Omega$) $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	20 20	27		20 20	27		V
A_{vd}	Large signal voltage gain $R_L = 10k\Omega$, $V_o = \pm 10V$, $T_{amb} = +25^{\circ}C$ $T_{min} \leq T_{amb} \leq T_{max}$	4 4	6		4 4	6		V/mV
GBP	Gain bandwidth product $T_{amb} = +25^{\circ}C$, $R_L = 10k\Omega$, $C_L = 100pF$		1			1		MHz
R_i	Input resistance		10^{12}			10^{12}		Ω
CMR	Common mode rejection ratio $R_S = 50\Omega$	80	86		80	86		dB

Table 4. $V_{CC} = \pm 15V$, $T_{amb} = +25^{\circ}C$ (unless otherwise specified) (continued)

Symbol	Parameter	TL062AC, AI, AM			TL062BC, BI, BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
SVR	Supply voltage rejection ratio $R_S = 50\Omega$	80	95		80	95		dB
I_{CC}	Supply current, no load $T_{amb} = +25^{\circ}C$, no load, no signal		200	250		200	250	μA
V_{o1}/V_{o2}	Channel separation $A_v = 100$, $T_{amb} = +25^{\circ}C$		120			120		
P_D	Total power consumption $T_{amb} = +25^{\circ}C$, no load, no signal		6	7.5		6	7.5	mW
SR	Slew rate $V_i = 10V$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_v = 1$	1.5	3.5		1.5	3.5		$V/\mu s$
t_r	Rise time $V_i = 20mV$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_v = 1$		0.2			0.2		μs
K_{ov}	Overshoot factor (see Figure 15) $V_i = 20mV$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_v = 1$		10			10		%
e_n	Equivalent input noise voltage $R_S = 100\Omega$, $f = 1kHz$		42			42		$\frac{nV}{\sqrt{Hz}}$

1. The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

Figure 20. DIP8 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			5.33			0.210
A1	0.38			0.015		
A2	2.92	3.30	4.95	0.115	0.130	0.195
b	0.36	0.46	0.56	0.014	0.018	0.022
b2	1.14	1.52	1.78	0.045	0.060	0.070
c	0.20	0.25	0.36	0.008	0.010	0.014
D	9.02	9.27	10.16	0.355	0.365	0.400
E	7.62	7.87	8.26	0.300	0.310	0.325
E1	6.10	6.35	7.11	0.240	0.250	0.280
e		2.54			0.100	
eA		7.62			0.300	
eB			10.92			0.430
L	2.92	3.30	3.81	0.115	0.130	0.150

The figure contains three technical drawings of the DIP8 package. The top drawing shows a front-side view with dimensions A, A1, A2, b, b2, c, D, E, E1, e, eA, eB, and L. The middle drawing shows a side view with dimensions E, c, eA, eB, and H. The bottom drawing shows a cross-sectional view with a dimension of 0.38 labeled 'GAUGE PLANE 0.38'.

Figure 21. SO-8 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
H	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	1°		8°	1°		8°
ccc			0.10			0.004

The diagram illustrates the mechanical dimensions of the SO-8 package. It includes a top view showing the footprint with pins numbered 1 through 8, and side views showing the profile and lead spacing. Cross-sectional views at the top and bottom show the lead profile, lead height (h), lead angle (hx45°), seating plane, gage plane, and lead length (L). Key dimensions labeled include A, A1, A2, b, c, D, E1, e, h, L, L1, and the lead profile angle hx45°.

6 Ordering information

Table 5. Order codes

Part number	Temperature range	Package	Packing	Marking
TL062MN TL062AMN TL062BMN	-55°C, +125°C	DIP8	Tube	TL062MN TL062AMN TL062BMN
TL062MD/MDT TL062AMD/AMDT TL062BMD/BMDT		SO-8	Tube or tape & reel	062M 062AM 062BM
TL062IN TL062AIN TL062BIN		DIP8	Tube	TL062IN TL062AIN TL062BIN
TL062ID/IDT TL062AID/AIDT TL062BID/BIDT	-40°C, +105°C	SO-8	Tube or tape & reel	062I 062AI 062BI
TL062CN TL062ACN TL062BCN		DIP8	Tube	TL062CN TL062ACN TL062BCN
TL062CD/CDT TL062ACD/ACDT TL062BCD/BCDT		SO-8	Tube or tape & reel	062C 062AC 062BC